Current-Voltage Characteristics, Small-Signal Parameters, Switching Times and Power-Delay Products of GaAs MESFET's

M.S. Shur and L.F. Eastman. "Current-Voltage Characteristics, Small-Signal Parameters, Switching Times and Power-Delay Products of GaAs MESFET's." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 150-152.

New simple computer and analytical models of GaAs MESFET's are proposed. The models are based on the assumption that the current saturation in GaAs MESFETs is related to the stationary Gunn domain formation at the drain side of the gate rather than to a pinch-off of the conducting channel under the gate. The results of the calculation are in good agreement with experimental data. The models can be used for a computer-aided design of GaAs integrated circuits.

❑ Return to main document.